

4K × 4 CMOS TAGRAM™

- 4K × 4 SRAM WITH ONBOARD 4 BIT COM-PARATOR
- 20, 25, AND 35ns ADDRESS TO COMPARE AC-CESS TIME
- 12, 15, AND 20ns TAG DATA TO COMPARE AC-CESS TIME
- EQUAL ACCESS, READ AND WRITE CYCLE TIMES
- FLASH CLEAR FUNCTION
- 22-PIN, 300 MIL PLASTIC AND CERAMIC DIP
- ALL INPUTS AND OUTPUTS ARE TTL COMPAT-IBLE, LOW CAPACITANCE, AND PROTECTED AGAINST STATIC DISCHARGE
- WORD WIDTH EXPANDABLE

TRUTH TABLE

WE	OE	CLR	MATCH	MODE
н	н	н	Valid	Compare Cycle
L	X	Н	Invalid	Write Cycle
н	L	Н	Invalid	Read Cycle
X	X	L	Invalid	Flash Clear Cycle

X = Don't Care

DESCRIPTION

The MK41H80 is a member of SGS-THOMSON's 4K × 4 CMOS Static RAM family featuring fully static operation requiring no external clocks or timing strobes. Cycle Time and Compare Access Time are equal. The MK41H80 is powered by a single +5V \pm 10% power supply and the inputs and outputs are fully TTL compatible.

The MK41H80 features an onboard 4 bit comparator that compares RAM contents and current input data. The result is an active high match on the MATCH pin or an active low miss on the MATCH pin. The MATCH pins of several MK41H80's can be nanded together to provide enabling or acknowledging signals to the data cache or processor.

Tag data can be read from the data pins by bringing Output Enable (OE) low. This will allow data





PIN NAMES

A ₀ - A ₁₁	- Address Inputs	
$DQ_0 - DQ_3$	- Data Input/Output	
MATCH	- Comparator Output	
WE	- Write Enable	
OE	- Output Enable	
CLR	- Flash Clear	
V _{cc}	- Power (+5V)	
V _{SS}	- Ground	

stored in the memory array to be displayed at the Outputs (DQ_0-DQ_3) .

Flash Clear operation is provided on the MK41H80 via the (CLR) pin. A low applied to the CLR pin clears all RAM bits to a logic zero.



FIGURE 2. COMPARE AND WRITE CYCLE

FIGURE 3. WRITE AND READ CYCLE





COMPARE, WRITE AND READ TIMING

The MK41H80 employs three signals for device control. The Write Enable (WE) pin enables a Write Cycle if low and either a Compare Cycle or a Read Cycle when high. The OE pin enables a Read Cycle if low or a Compare Cycle if high. The CLR pin enables a Flash Clear Cycle when brought low.

The MK41H80 begins a Compare Cycle with the application of a valid address (see Figure 2). A valid MATCH is enabled when OE and WE go high in conjunction with their respective Set Up and Hold times. MATCH will occur t_{ACA} after a valid address, and t_{DCA} after valid Data In. MATCH will then go invalid t_{ACH} after the address changes.

The MK41H80 starts a Write Cycle with stable addresses (see Figure 2). \overline{OE} may be in either logic state. WE may fall with stable addresses, and must remain low until t_{AW} with a duration of t_{WEW} . Data in must be held valid t_{DS} before and t_{DH} after WE goes high. MATCH will be invalid during this cycle.

The MK41H80 begins a Read Cycle with stable addresses and WE high (see Figure 3). DQ becomes valid t_{AA} after a valid address, and t_{OEA} after the fall of OE. DQ outputs become invalid t_{OH} after the address becomes invalid or t_{OEZ} after OE is brought high. Ripple through data access may be accomplished by holding OE active low while strobing addresses A_0 - A_{11} , and holding CLR and WE high. The MATCH output will be invalid during the Read cycle.

ELECTRICAL	CHARACTERIS	ICS AND	RECOMMENDED	AC OPERATIN	G CONDITIONS
$(0^{\circ}C \leq T_{A} \leq 70)$	°C) (V _{CC} = 5.0V	±10%)			

		-20		-25		-35			
SYMBOL	PARAMETER	MIN	MAX	MIN	MAX	MIN	MAX	UNITS	NOTES
tc	Cycle Time			25		35		ns	
tccs	Compare Command Set Up Time	7		8		10	1	ns	
tссн	Compare Command Hold Time	0		0		0		ns	
t _{RCS}	Read Command (WE) Set Up Time	0		0		0		ns	
t _{RCH}	Read Command (WE) Hold Time	0		0		0		ns	
tAS	Address Set-up Time	0		0		0		ns	
t _{AW}	Address Stable to End of Write Command (WE)	16		20		30		ns	
t _{AH}	Address Hold Time after End of Write	0		0		0		ns	
twew	Write Command (WE) to End of Write			20		30		ns	
tos	Data Set Up Time			13		14		ns	
t _{DH}	Data Hold Time	0		0		0		ns	
t _{DCA}	Data Compare Access Time		12		15		20	ns	3
tACA	Address Compare Access Time		20		25		35	ns	3
t _{ACH}	Address Compare Hold Time	5		5		5		ns	3
t _{DCH}	Data Compare Hold Time	3		3		3		ns	3
t _{OEA}	Output Enable (OE) Access Time		10		12		15	ns	3
t _{он}	Valid Data Out (DQ) Hold Time	5		5		5		ns	3
t _{AA}	Address Access Time		20		25		35	ns	3
tOEZ	Output Enable (OE) to High-Z		7		8		10	ns	4
tOEL	Output Enable (OE) to Low-Z	2		2		2		ns	4
twez	Write Enable (WE) to High-Z		8		10		13	ns	4
twel	Write Enable (WE) to Low-Z	5		5		5		ns	4

SGS-THOMSON

APPLICATION

The MK41H80 operates from a 5.0 volt supply. It is compatible with all standard TTL families on all inputs and outputs. The device should share a solid ground plane with any other devices interfaced with it, particularly TTL devices. Additionally, because the outputs can drive rail-to-rail into high impedance loads, the MK41H80 can also interface to 5 volt CMOS on all inputs and outputs. Refer to the normalized performance curves that follow.

The MK41H80 compares contents of addressed RAM locations to the current data inputs. A logic one (1) output on the MATCH pin indicates that the input data and the RAM contents match. Conversely, a logic zero (0) on the MATCH pin indicates at least one bit difference between the RAM contents and input data generating a miss.

The MATCH output is always at either an active high or low logic level, and does not exhibit a threestate or high impedance characteristic. Since the comparator circuitry is always enabled, metastable data input levels can result in excessive MATCH out put activity. Therefore, the use of pull-up or pulldown resistors is recommended on the data bus.

A pull-up resistor is also recommended for the CLR input. This will ensure that any low going system noise, coupled onto the input, does not drive CLR below V_{IH} minimum specifications.

Because high frequency current transients will be associated with the operation of the MK41H80, power lines inductance must be minimized on the circuit board power distribution network. Power and ground trace gridding or separate power planes can be employed to reduce line inductance.

Though often times not thought of as such, the traces on a memory board are basically unterminated, low impedance transmission lines. As such they are subject to signal reflections manifested as noise, undershoots and excessive ringing. Series termination in close proximity to the TTL drivers can improve driver/signal path impedance matching. While experimentation most often proves to be the only practical approach to selection of series resistors, values in the range of 10 to 33 ohms often prove most suitable.



FIGURE 4. BLOCK DIAGRAM

FLASH CLEAR CYCLE

A Flash Clear Cycle begins as CLR is brought low (see Figure 5). A Flash Clear sets all 16,384 bits in the RAM to logic zero. Control Inputs will not be

recognized from t_{CX} after CLR falls to t_{CR} after CLR is brought high. OE and WE are Don't Cares and DQ is High-Z. MATCH will be invalid while CLR is low.

AC ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS (0 $^\circ\!C\!\le\!T_A\!\le\!70\,^\circ\!C$) (V_{CC} = 5.0V $\pm10\%$)

		-2	0	-2	25	-3	15		
SYMBOL	PARAMETER	MIN	MAX	MIN	MAX	MIN	MAX	UNITS	NOTES
1FCC	Flash Clear Cycle Time	40		50		70		ns	
texe	Clear (CLR) to Inputs Don't Care	0		0		0		ns	
¹ CR	End of Clear (CLR) to Inputs Recognized	0		0		0		ns	
t _{CLP}	Flash Clear (CLR) Pulse Width	36		44		60		ns	

Figure 5. Read-Flash Clear-Write Cycle



ABSOLUTE MAXIMUM RATINGS

Voltage on Any Terminal Relative to V _{SS}	1.0V to +7.0V
Operating Temperature T _A (Ambient)	0℃ to +70℃
Storage Temperature (Ceramic)	−65°C to +150°C
Storage Temperature (Plastic)	−55°C to +125°C
Power Dissipation	1 Watt
Output Current per Pin	
Stresses greater than those listed under "Absolute Maximum Ratings" may cause	permanent damage to the device. This
is a stress rating only and functional operation of the device at these or any other	conditions above those indicated in the
operation sections of this specification is not implied. Exposure to absolute maximu	im rating conditions for extended periods

RECOMMENDED DC OPERATING CONDITIONS

(0°C≤T_A≤+70°C)

of time may affect reliability.

SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	NOTES
V _{CC}	Supply Voltage (Referenced to V _{SS})	4.5	5.0	5.5	V	
V _{SS}	Ground	0.0	0.0	0.0	V	
VIH	Input High (Logic 1) voltage, All Inputs (Referenced to V_{SS})	2.2		V _{CC} +0.3	V	
VIL	Input Low (Logic 0) voltage, All Inputs (Referenced to $\rm V_{SS})$	-0.3		0.8	V	

DC ELECTRICAL CHARACTERISTICS

 $(0^{\circ}C \le T_A \le +70^{\circ}C) (V_{CC} = 5.0V \pm 10\%)$

SYMBOL	PARAMETER	MIN	MAX	UNITS	NOTES
I _{CC1}	Operating Current - Average Power Supply Operating Current		120	mA	1
ΓL	Input Leakage Current, Any input	-1	1	μA	5
IOL	Output Leakage Current	-10	10	μA	6
V _{OH}	Output High (Logic 1) voltage Referenced to V_{SS} ; $I_{OH} = -4mA$	2.4		V	
V _{OL}	Output Low (Logic 0) voltage Referenced to V_{SS} ; $I_{OL} = +8mA$		0.4	V	

AC ELECTRICAL CHARACTERISTICS

 $(T_A = 25 \,^{\circ}C, f = 1.0 \text{ MHz})$

SYMBOL	PARAMETER	ТҮР	MAX	UNITS	NOTES
C ₁	Capacitance on any Input Pin	4	5	pF	2
C ₂	Capacitance on any Output Pin	8	10	pF	2

AC TEST CONDITIONS

Input Levels	. GND	to 3.0 V
Transition Times		5 ns
Input and Output Signal Timing Reference Level		1.5 V
Ambient Temperature	0°C	to 70°C
V _{cc}	± 10	percent

FIGURE 6. OUTPUT LOAD CIRCUITS



- 2. Capacitances are sampled and not 100% tested.
- 3. Measured with load shown In Figure 6(A)
- 4. Measured with load shown in Figure 6(B)

 Output leakage current specifications are valid for all DQs such that OV < V_{OUT} < V_{CC} With exception to MATCH which is always enabled.

NORMALIZED DC AND AC PERFORMANCE CHARACTERISTICS





NORMALIZED DC AND AC PERFORMANCE CHARACTERISTICS





NORMALIZED DC AND AC PERFORMANCE CHARACTERISTICS







Notes

2

3

Max

210 2

.140

021

.070

012 3

1.050 1

025

325

270

110

400

22 PIN "P" PACKAGE, SIDE BRAZED CERAMIC DIP



ORDERING INFORMATION

PART NUMBER	ACCESS TIME	PACKAGE TYPE	TEMPERATURE RANGE
MK41H80N-20	20 ns	22 pin Plastic DIP	0°C to 70°C
MK41H80N-25	25 ns	22 pin Plastic DIP	0°C to 70°C
MK41H80N-35	35 ns	22 pin Plastic DIP	0°C to 70°C
MK41H80P-20	20 ns	22 pin Ceramic DIP	0°C to 70°C
MK41H80P-25	25 ns	22 pin Ceramic DIP	0°C to 70°C
MK41H80P-35	35 ns	22 pin Ceramic DIP	0°C to 70°C



